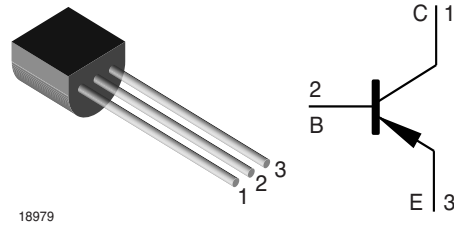


Small Signal Transistors (PNP)

Features

- PNP Silicon Epitaxial Planar Transistors for switching and AF amplifier applications.
- These transistors are subdivided into three groups A, B, and C according to their current gain. The type BC556 is available in groups A and B, however, the types BC557 and BC558 can be supplied in all three groups. As complementary types, the NPN transistors BC546...BC548 are recommended.
- On special request, these transistors are also manufactured in the pin configuration TO-18.



Mechanical Data

Case: TO-92 Plastic case

Weight: approx. 177 mg

Packaging Codes/Options:

BULK / 5 k per container 20 k/box

TAP / 4 k per Ammopack 20 k/box

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Collector - base voltage		BC556	$-V_{CBO}$	80	V
		BC557	$-V_{CBO}$	50	V
		BC558	$-V_{CBO}$	30	V
			$-V_{CBO}$	30	V
Collector - emitter voltage		BC556	$-V_{CES}$	80	V
		BC557	$-V_{CES}$	50	V
		BC558	$-V_{CES}$	30	V
			$-V_{CES}$	30	V
			$-V_{CEO}$	65	V
			$-V_{CEO}$	45	V
			$-V_{CEO}$	30	V
			$-V_{CEO}$	30	V
Emitter - base voltage			$-V_{EBO}$	5	V
Collector current			$-I_C$	100	mA
Peak collector current			$-I_{CM}$	200	mA
Peak emitter current			$-I_{EM}$	200	mA
Power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$		P_{tot}	500 ¹⁾	mW
Peak base current			$-I_{BM}$	200	mA

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air		$R_{\theta JA}$	250 ¹⁾	°C/W
Junction temperature		T_j	150	°C
Storage temperature range		T_S	- 65 to + 150	°C

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

Electrical DC Characteristics

Parameter	Test condition	Part	Symbol	Min	Typ	Max	Unit
Small signal current gain (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{fe}			220	
Small signal current gain (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{fe}			330	
Small signal current gain (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{fe}			600	
Input impedance (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{ie}	1.6	2.7	4.5	k Ω
Input impedance (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{ie}	3.2	4.5	8.5	k Ω
Input impedance (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{ie}	6	8.7	15	k Ω
Output admittance (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{oe}		18	30	μS
Output admittance (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{oe}		30	60	μS
Output admittance (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{oe}		60	110	μS
Reverse voltage transfer ratio (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{re}		1.5×10^{-4}		
Reverse voltage transfer ratio (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{re}		2×10^{-4}		
Reverse voltage transfer ratio (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$		h_{re}		3×10^{-4}		
DC current gain (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ }\mu\text{A}$		h_{FE}		90		
DC current gain (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ }\mu\text{A}$		h_{FE}		150		
DC current gain (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 10\text{ }\mu\text{A}$		h_{FE}		270		
DC current gain (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$		h_{FE}	110	180	220	
DC current gain (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$		h_{FE}	200	290	450	
DC current gain (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 2\text{ mA}$		h_{FE}	420	500	800	
DC current gain (current gain group A)	- $V_{CE} = 5\text{ V}$, - $I_C = 100\text{ mA}$		h_{FE}		120		
DC current gain (current gain group B)	- $V_{CE} = 5\text{ V}$, - $I_C = 100\text{ mA}$		h_{FE}		200		
DC current gain (current gain group C)	- $V_{CE} = 5\text{ V}$, - $I_C = 100\text{ mA}$		h_{FE}		400		
Collector saturation voltage	- $I_C = 10\text{ mA}$, - $I_B = 0.5\text{ mA}$		V_{CEsat}		80	300	mV
	- $I_C = 100\text{ mA}$, - $I_B = 5\text{ mA}$		V_{CEsat}		250	650	mV

Parameter	Test condition	Part	Symbol	Min	Typ	Max	Unit
Base saturation voltage	- $I_C = 10 \text{ mA}$, - $I_B = 0.5 \text{ mA}$		V_{BEsat}		700		mV
	- $I_C = 100 \text{ mA}$, - $I_B = 5 \text{ mA}$		V_{BEsat}		900		mV
Base - emitter voltage	- $V_{CE} = 5 \text{ V}$, - $I_C = 2 \text{ mA}$		V_{BE}	600	660	700	mV
	- $V_{CE} = 5 \text{ V}$, - $I_C = 10 \text{ mA}$		V_{BE}			800	mV
Collector-emitter cut-off current	- $V_{CE} = 80 \text{ V}$	BC556	I_{CES}		0.2	15	nA
	- $V_{CE} = 50 \text{ V}$	BC557	I_{CES}		0.2	15	nA
	- $V_{CE} = 30 \text{ V}$	BC558	I_{CES}		0.2	15	nA
	- $V_{CE} = 80 \text{ V}$, $T_j = 125 \text{ }^\circ\text{C}$	BC556	I_{CES}			4	μA
	- $V_{CE} = 50 \text{ V}$, $T_j = 125 \text{ }^\circ\text{C}$	BC557	I_{CES}			4	μA
	- $V_{CE} = 30 \text{ V}$, $T_j = 125 \text{ }^\circ\text{C}$	BC558	I_{CES}			4	μA
		BC559	I_{CES}			4	μA

Electrical AC Characteristics

Parameter	Test condition	Part	Symbol	Min	Typ	Max	Unit
Gain bandwidth product	- $V_{CE} = 5 \text{ V}$, - $I_C = 10 \text{ mA}$, $f = 100 \text{ MHz}$		f_T		150		MHz
Collector - base capacitance	- $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$		C_{CBO}			6	pF
Noise figure	- $V_{CE} = 5 \text{ V}$, - $I_C = 200 \mu\text{A}$, $R_G = 2 \text{ k}\Omega$, $f = 1 \text{ kHz}$, $\Delta f = 200 \text{ Hz}$	BC556	F		2	10	dB
		BC557	F		2	10	dB
		BC558	F		2	10	dB
		BC559	F		1	4	dB
		- $V_{CE} = 5 \text{ V}$, - $I_C = 200 \mu\text{A}$, $R_G = 2 \text{ k}\Omega$, $f = (30 \text{ to } 15000) \text{ Hz}$	BC559	F		1.2	4

Typical Characteristics ($T_{amb} = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

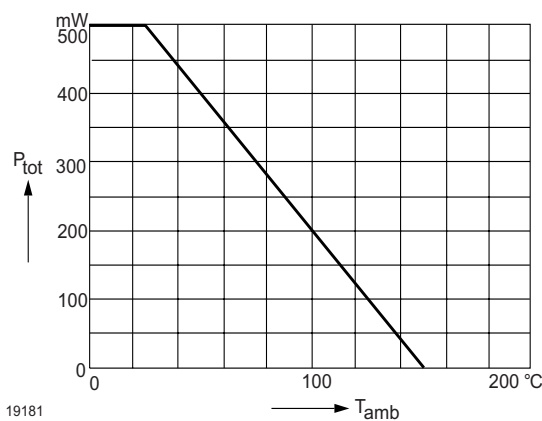


Figure 1. Admissible Power Dissipation vs. Ambient Temperature

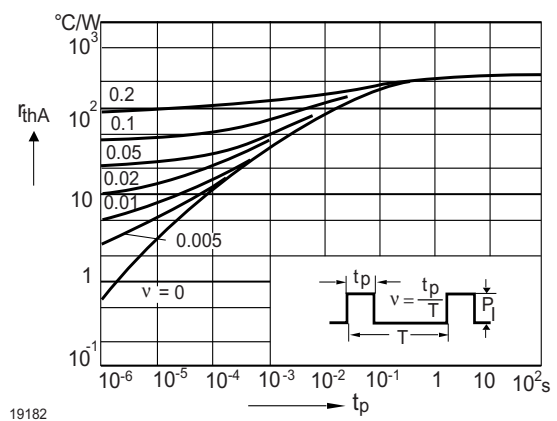


Figure 2. Pulse Thermal Resistance vs. Pulse Duration

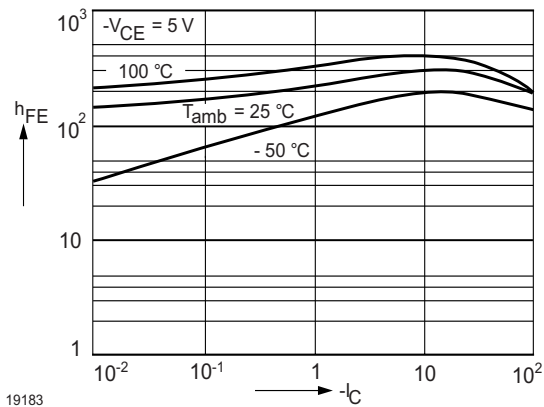


Figure 3. DC Current Gain vs. Collector Current

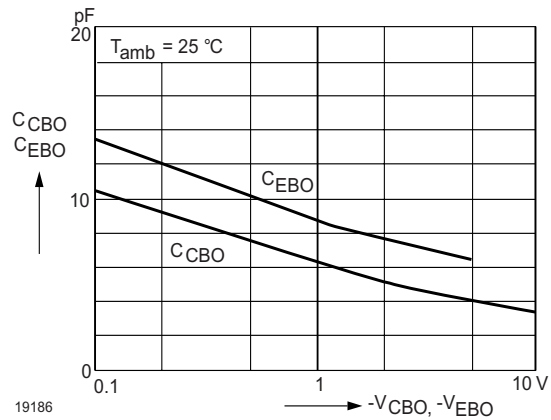


Figure 6. Collector Base Capacitance, Emitter base Capacitance vs. Bias Voltage

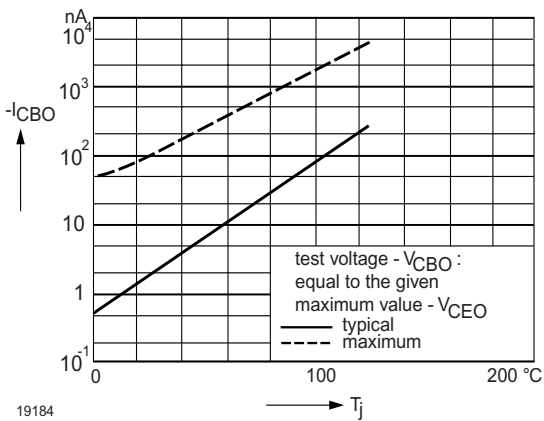


Figure 4. Collector-Base Cutoff Current vs. Ambient Temperature

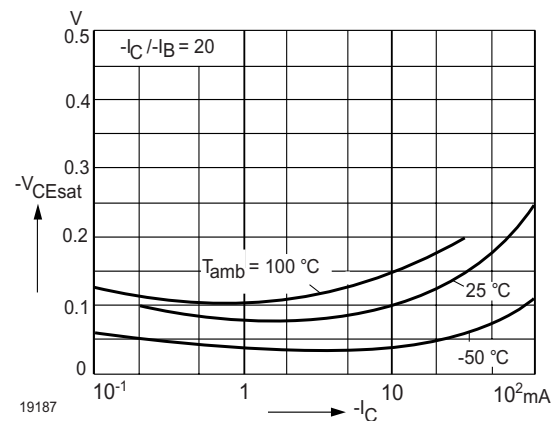


Figure 7. Collector Saturation Voltage vs. Collector Current

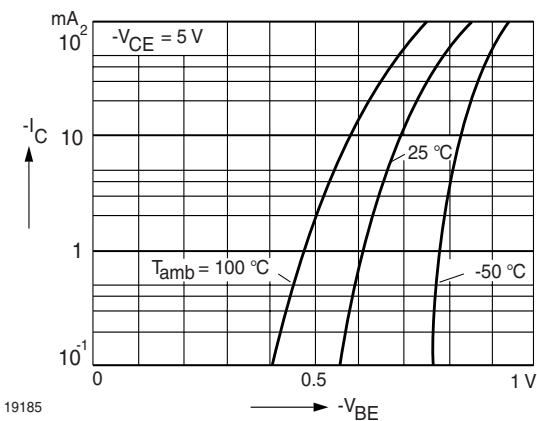


Figure 5. Collector Current vs. Base-Emitter Voltage

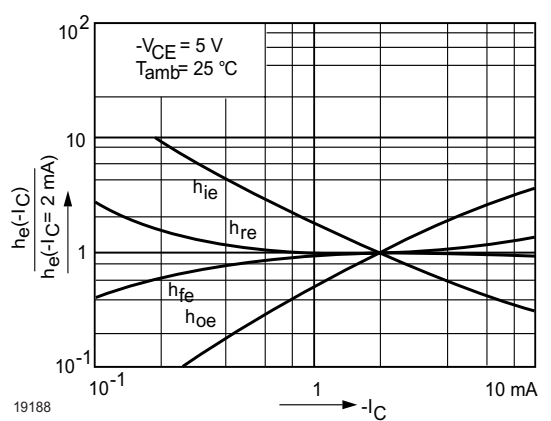


Figure 8. Relative h-Parameters vs. Collector Current

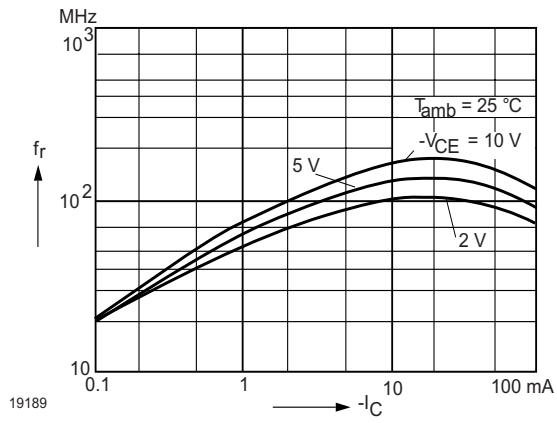


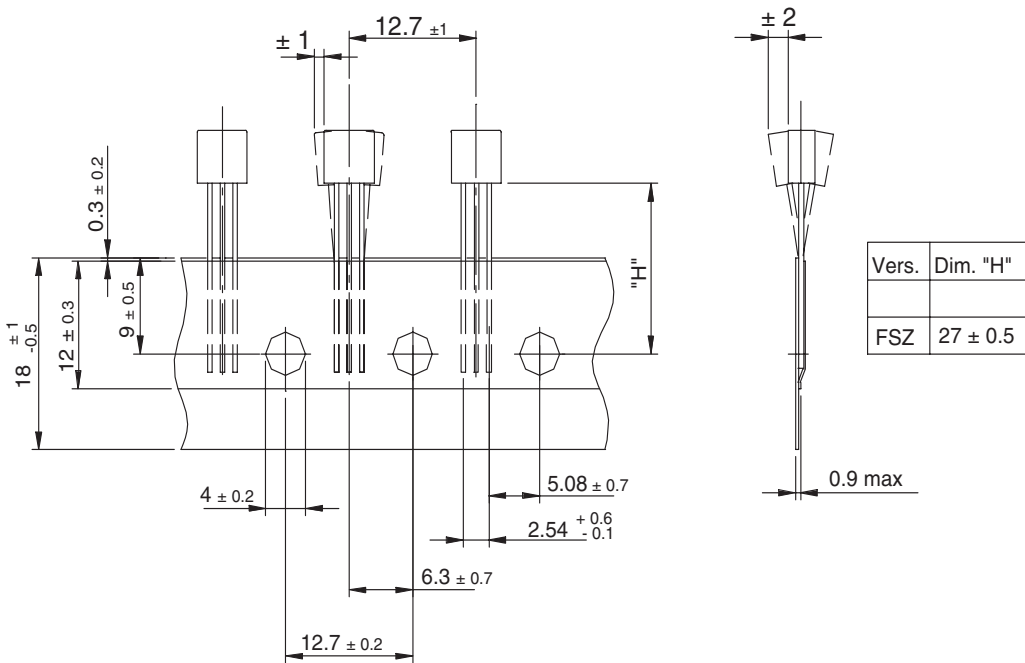
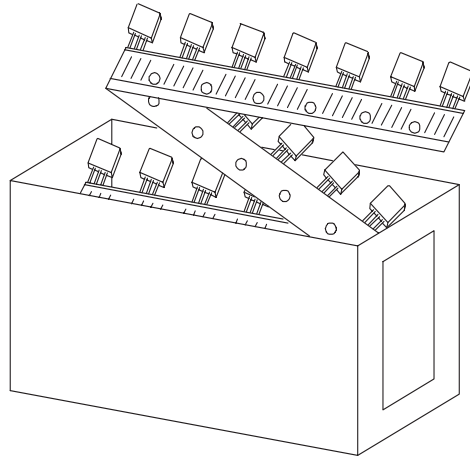
Figure 9. Gain-Bandwidth Product vs. Collector Current

BC556 to BC558

Vishay Semiconductors



Packaging for Radial Taping

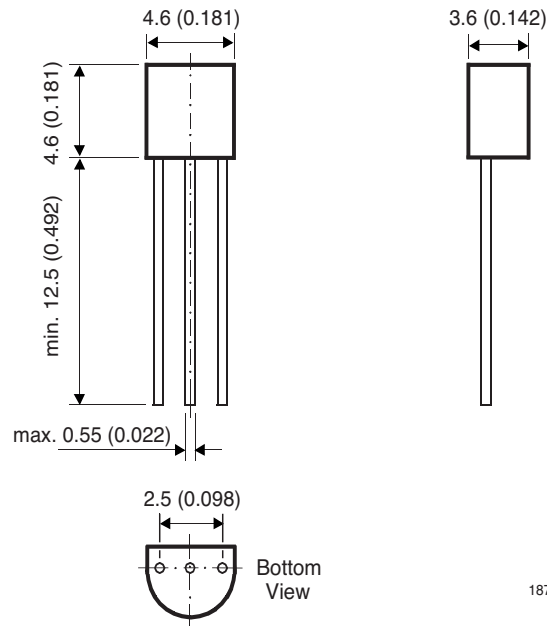


Vers.	Dim. "H"
FSZ	27 ± 0.5

Measure limit over 20 index - holes: ± 1

18787

Package Dimensions in mm (Inches)



18776

Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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